

# **HD74HC1G32**

# 2-input OR Gate

REJ03D0187-0500Z (Previous ADE-205-313C (Z)) Rev.5.00 Jan.27.2004

#### **Description**

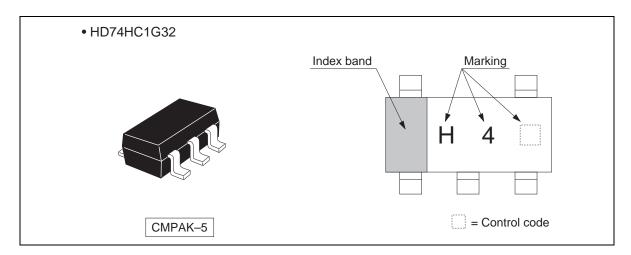
The HD74HC1G32 is high speed CMOS two input OR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

#### **Features**

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC32 Supply voltage range : 2 to 6 V
  - Operating temperature range: -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC1G32CME	CMPAK-5 pin	CMPAK-5V	CM	E (3,000 pcs/reel)

#### **Outline and Article Indication**



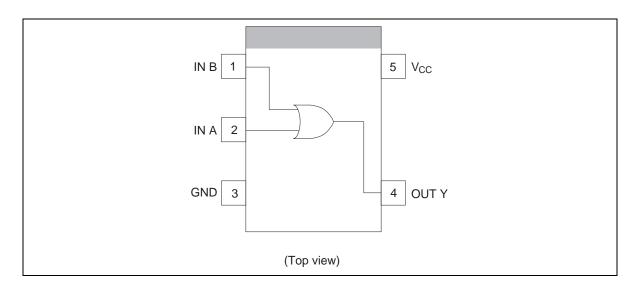
### **Function Table**

#### Inputs

A	В	Output Y
L	L	L
Н	L	Н
L	Н	Н
Н	Н	Н

H : High level L : Low level

# **Pin Arrangement**



#### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage range *1	Vı	$-0.5$ to $V_{CC}$ + 0.5	V	
Output voltage range *1, 2	Vo	$-0.5$ to $V_{CC}$ + 0.5	V	Output : H or L
Input clamp current	I <sub>IK</sub>	±20	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I <sub>OK</sub>	±20	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I <sub>O</sub>	±25	mA	$V_O = 0$ to $V_{CC}$
Continuous current through V <sub>CC</sub> or GND	I <sub>CC</sub> or I <sub>GND</sub>	±25	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	2	6	V	
Input voltage range	Vı	0	V <sub>CC</sub>	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Output current	I <sub>OL</sub>	_	2.0	mA	$V_{CC} = 4.5 \text{ V}$
		_	2.6		$V_{CC} = 6.0 \text{ V}$
	I <sub>OH</sub>	_	-2.0	mA	$V_{CC} = 4.5 \text{ V}$
		_	-2.6		$V_{CC} = 6.0 \text{ V}$
Input rise / fall time	t <sub>r</sub> , t <sub>f</sub>	0	1000	ns	V <sub>CC</sub> = 2.0 V
(10% to 90%)	% to 90%) 0 500		<del></del>	$V_{CC} = 4.5 \text{ V}$	
		0	400		$V_{CC} = 6.0 \text{ V}$
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

#### HD74HC1G32

# **Electrical Characteristics**

		$\mathbf{V}_{CC}$	$T_a = 25$ °C $T_a$		$T_a = -4$	10 to 85°C				
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Cond	ditions
Input voltage	V <sub>IH</sub>	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_	-		
		6.0	4.2	_	_	4.2	_	=		
	V <sub>IL</sub>	2.0	_	_	0.5	_	0.5	=		
		4.5	_	_	1.35	_	1.35	=		
		6.0	_	_	1.8	_	1.8	=		
Output voltage	V <sub>OH</sub>	2.0	1.9	2.0	_	1.9	_	V	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_	="		
		6.0	5.9	6.0	_	5.9	_	=		
		4.5	4.18	4.31	_	4.13	_	<del>-</del> -		$I_{OH} = -2 \text{ mA}$
		6.0	5.68	5.80	_	5.63	_			$I_{OH} = -2.6 \text{ mA}$
	V <sub>OL</sub>	2.0	_	0.0	0.1	_	0.1	_		$I_{OL} = 20 \mu A$
		4.5	_	0.0	0.1	_	0.1	=		
		6.0	_	0.0	0.1	_	0.1	=		
		4.5	_	0.17	0.26	_	0.33	=		I <sub>OL</sub> = 2 mA
		6.0	_	0.18	0.26	_	0.33	-		I <sub>OL</sub> = 2.6 mA
Input current	I <sub>IN</sub>	6.0	_	_	±0.1	_	±1.0	μΑ	$V_{IN} = V_{CC}$	or GND
Operating current	I <sub>CC</sub>	6.0	_	_	1.0	_	10.0	μΑ	$V_{IN} = V_{CC}$	or GND

#### **Switching Characteristics**

 $Ta = 25^{\circ}C$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub> t <sub>THL</sub>	_	5	10	ns	Test circuit
Propagation delay time	t <sub>PLH</sub> t <sub>PHL</sub>	_	7	15	ns	Test circuit

 $C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V}$ 

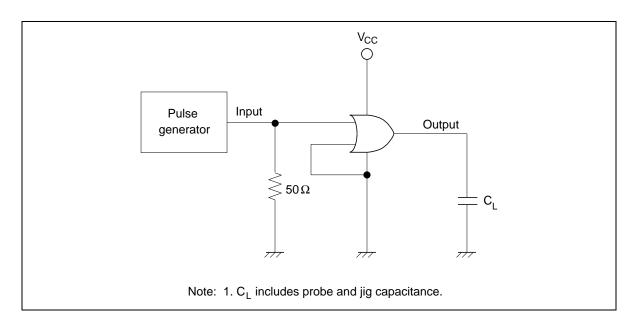
		$\mathbf{V}_{\text{CC}}$	Ta = 25°C		$Ta = -40 \text{ to } 85^{\circ}\text{C}$				
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub>	2.0	_	50	125	_	155	ns	Test circuit
	$t_{THL}$	4.5	_	14	25	_	31	_	
		6.0	_	12	21	_	26	_	
Propagation delay time	t <sub>PLH</sub>	2.0	_	48	100	_	125	ns	Test circuit
	$t_{\text{PHL}}$	4.5	_	12	20	_	25	_	
		6.0	_	9	17	_	21	_	
Input capacitance	C <sub>IN</sub>	_	_	2.5	5	_	5	pF	
Equivalent capacitance	C <sub>PD</sub>			10	_	_	_	pF	

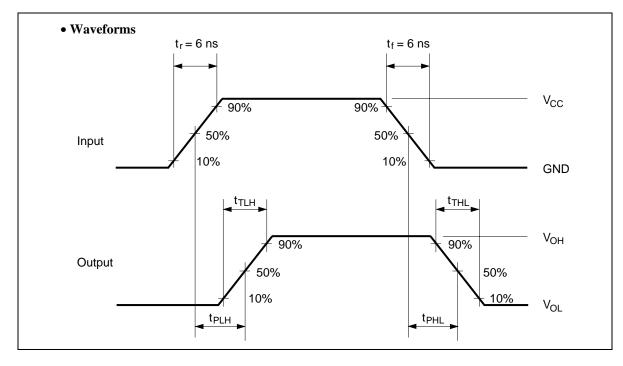
 $(C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$ 

Note: C<sub>PD</sub> is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

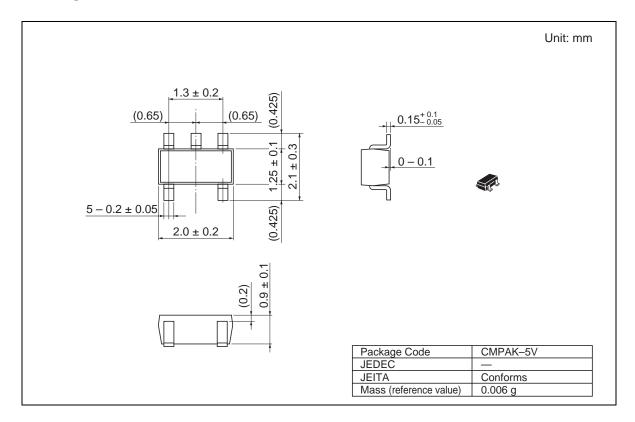
 $I_{CC}$  (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

#### **Test Circuit**





# **Package Dimensions**



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